

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Yi Ding
Assignee: Mosel Vitelic, Inc.
Title: Fabrication of Gate Dielectric In Nonvolatile Memories In Which A
Memory Cell Has Multiple Floating Gates
Application No.: Unassigned Filing Date: Filed Herewith
Examiner: Unassigned Group Art Unit: Unassigned
Docket No.: M-15230 US

San Jose, California
July 30, 2003

Mail Stop Patent Application
Commissioner For Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR § 1.97(b)

Dear Sir:

Pursuant to 37 CFR § 1.56, § 1.97 and § 1.98, the documents listed on the accompanying form PTO-1449 are called to the attention of the Examiner for the above patent application. Copies of these documents are enclosed.

Citation of these documents shall not be construed as:

1. an admission that the documents are necessarily prior art with respect to the instant invention;
2. a representation that a search has been made, other than as described above; or
3. an admission that the information cited herein is, or is considered to be material to patentability as defined in § 1.56(b).

No fee is believed to be required. If a fee is required for this Information Disclosure Statement, please charge the fee to Deposit Account No. 50-2257. This paper is being submitted in duplicate.

EXPRESS MAIL LABEL NO.:

EE 508 123 287 US

Respectfully submitted,

Michael Shenker

Michael Shenker
Attorney for Applicant(s)
Reg. No. 34,250

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(Use several sheets if necessary)				Yi Ding			
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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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Examiner			Date Considered				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.							

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